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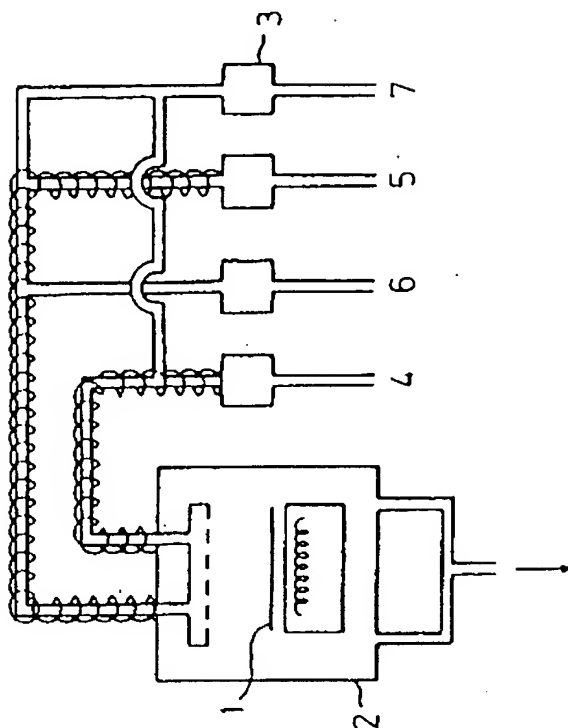
APPLICATION DATE : 06-06-84
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APPLICANT : FUJITSU LTD;

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TITLE : FORMATION OF
TUNGSTEN-ALUMINUM ALLOY FILM



ABSTRACT : PURPOSE: To form a W-Al alloy film having high adhesion to polysilicone and silicon oxide and low specific resistance by bringing tungsten hexafluoride, lower alkyl aluminum and hydrogen into a chemical vapor phase reaction under reduced pressure.

CONSTITUTION: A silicon substrate 1 in a reactor 2 is kept at 300-350°C, and tungsten hexafluoride 4, tributyl aluminum 5 and hydrogen 6 are fed to the reactor 2 at 2cc/min, 0.5-6cc/min and 20-100cc/min flow rates, respectively in a standard state each while controlling the flow rates with mass controllers 3 so as to maintain 0.1-10Torr internal pressure of the reactor 2. A W-Al alloy film is formed on the surface of the substrate 1.

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